

SOT-26

Pin Definition:

- | | |
|-------------|-------------|
| 1. Gate 1 | 6. Drain 1 |
| 2. Source 2 | 5. Source 1 |
| 3. Gate 2 | 4. Drain 2 |

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (m Ω) | I_D (A) |
|--------------|----------------------------|-----------|
| 20 | 55 @ $V_{GS} = 4.5V$ | 2.0 |
| | 70 @ $V_{GS} = 2.5V$ | 1.5 |
| | 110 @ $V_{GS} = 1.8V$ | 1.0 |

Features

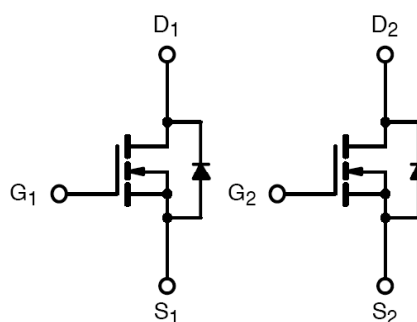
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switch
- PA Switch

Ordering Information

| Part No. | Package | Packing |
|----------------|---------|---------|
| TSM3900DCX6 RF | SOT-26 | T&R |

Block Diagram


Dual N-Channel MOSFET

Absolute Maximum Rating ($T_a = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|----------------|--------------------|------------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 8 | V |
| Continuous Drain Current | I_D | 2 | A |
| Pulsed Drain Current | I_{DM} | 8 | A |
| Continuous Source Current (Diode Conduction) ^{a,b} | I_S | 1.6 | A |
| Maximum Power Dissipation | P_D | $T_a = 25^\circ C$ | 2.0 |
| | | $T_a = 70^\circ C$ | 1.3 |
| Operating Junction Temperature | T_J | +150 | $^\circ C$ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ C$ |

Thermal Performance

| Parameter | Symbol | Limit | Unit |
|--|-----------------|-------|--------------|
| Junction to Case Thermal Resistance | $R_{\theta JC}$ | 30 | $^\circ C/W$ |
| Junction to Ambient Thermal Resistance (PCB mounted) | $R_{\theta JA}$ | 80 | $^\circ C/W$ |

Notes:

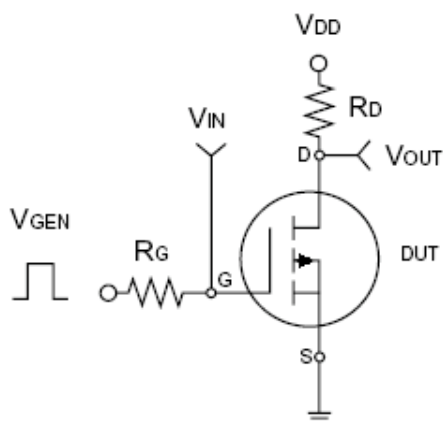
- Pulse width limited by the Maximum junction temperature
- Surface Mounted on FR4 Board, $t \leq 5$ sec.

Electrical Specifications

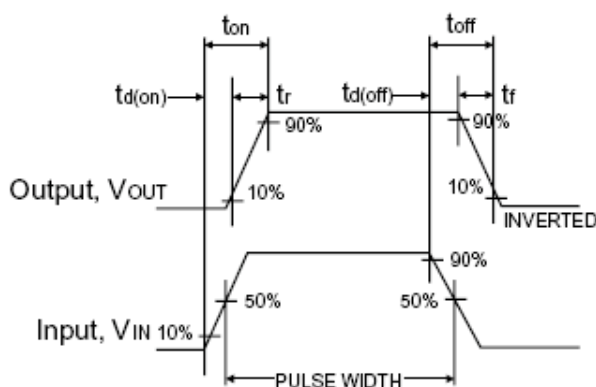
| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|----------------------------------|---|--------------|------|--------|-----------|------------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | BV_{DSS} | 20 | -- | -- | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | $V_{GS(TH)}$ | 0.65 | 0.95 | 1.2 | V |
| Gate Body Leakage | $V_{GS} = \pm 8V, V_{DS} = 0V$ | I_{GSS} | -- | -- | ± 100 | nA |
| Zero Gate Voltage Drain Current | $V_{DS} = 16V, V_{GS} = 0V$ | I_{DSS} | -- | -- | 1.0 | μA |
| On-State Drain Current | $V_{DS} \geq 5V, V_{GS} = 4.5V$ | $I_{D(ON)}$ | 5 | -- | -- | A |
| Drain-Source On-State Resistance | $V_{GS} = 4.5V, I_D = 2.0A$ | $R_{DS(ON)}$ | -- | 45 | 55 | m Ω |
| | $V_{GS} = 2.5V, I_D = 1.5A$ | | -- | 50 | 70 | |
| | $V_{GS} = 1.8V, I_D = 1.0A$ | | -- | 80 | 110 | |
| Forward Transconductance | $V_{DS} = 5V, I_D = 2.4A$ | g_{fs} | -- | 5 | -- | S |
| Diode Forward Voltage | $I_S = 1.6A, V_{GS} = 0V$ | V_{SD} | -- | 0.79 | 1.1 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | $V_{DS} = 10V, I_D = 2.4A, V_{GS} = 4.5V$ | Q_g | -- | 3.69 | -- | nC |
| Gate-Source Charge | | Q_{gs} | -- | 0.70 | -- | |
| Gate-Drain Charge | | Q_{gd} | -- | 1.06 | -- | |
| Input Capacitance | $V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$ | C_{iss} | -- | 427.12 | -- | pF |
| Output Capacitance | | C_{oss} | -- | 80.56 | -- | |
| Reverse Transfer Capacitance | | C_{rss} | -- | 57 | -- | |
| Switching^c | | | | | | |
| Turn-On Delay Time | $V_{DD} = 10V, R_L = 10\Omega, I_D = 1A, V_{GEN} = 4.5V, R_G = 6\Omega$ | $t_{d(on)}$ | -- | 6.16 | -- | nS |
| Turn-On Rise Time | | t_r | -- | 7.56 | -- | |
| Turn-Off Delay Time | | $t_{d(off)}$ | -- | 16.61 | -- | |
| Turn-Off Fall Time | | t_f | -- | 4.07 | -- | |

Notes:

- a. pulse test: $PW \leq 300\mu S$, duty cycle $\leq 2\%$
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



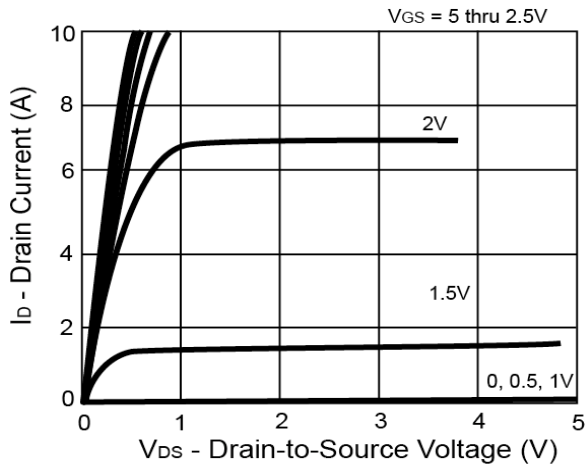
Switching Test Circuit



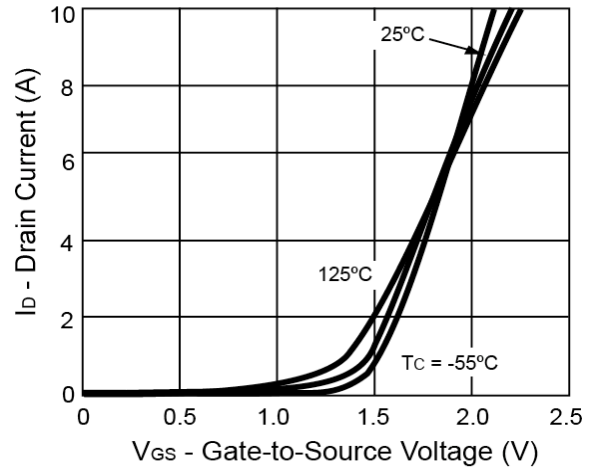
Switchin Waveforms

Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

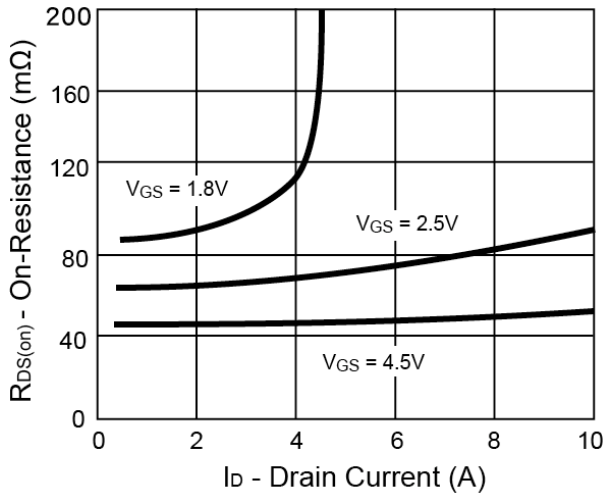
Output Characteristics



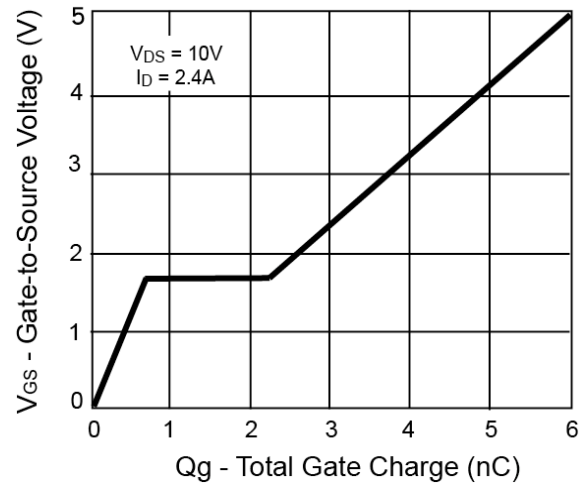
Transfer Characteristics



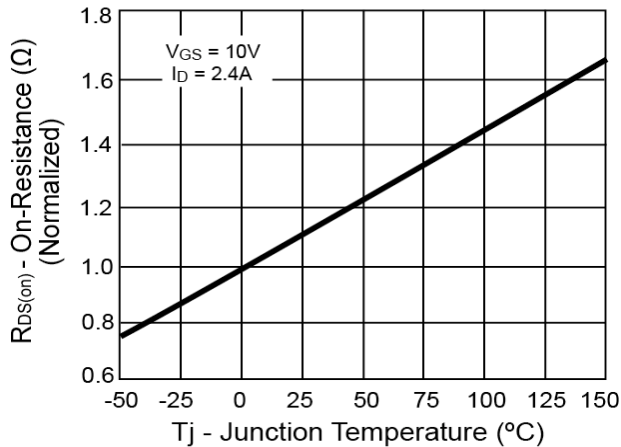
On-Resistance vs. Drain Current



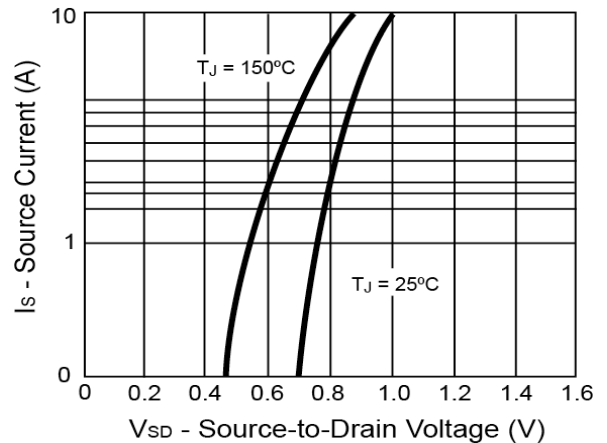
Gate Charge



On-Resistance vs. Junction Temperature

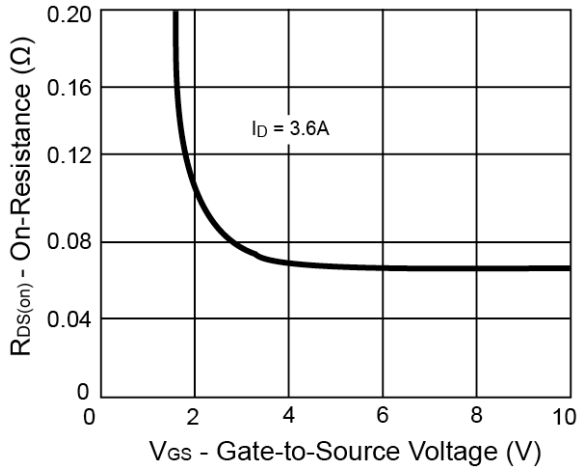


Source-Drain Diode Forward Voltage

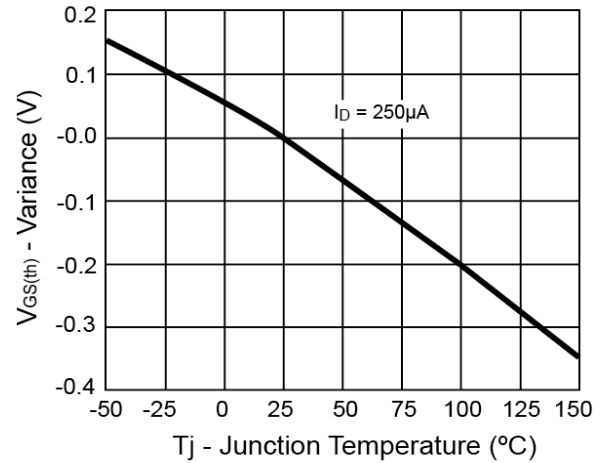


Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

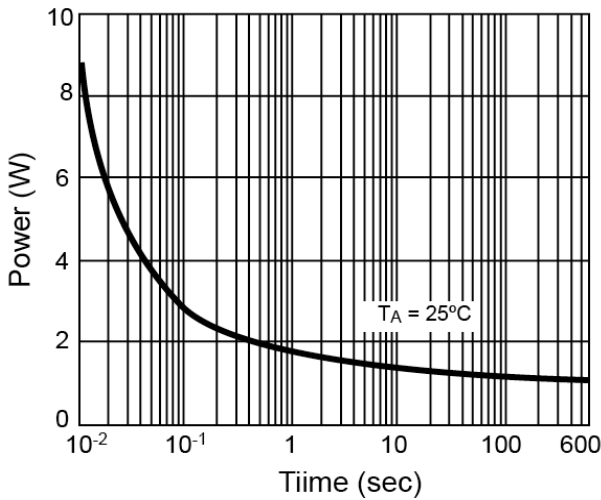
On-Resistance vs. Gate-Source Voltage



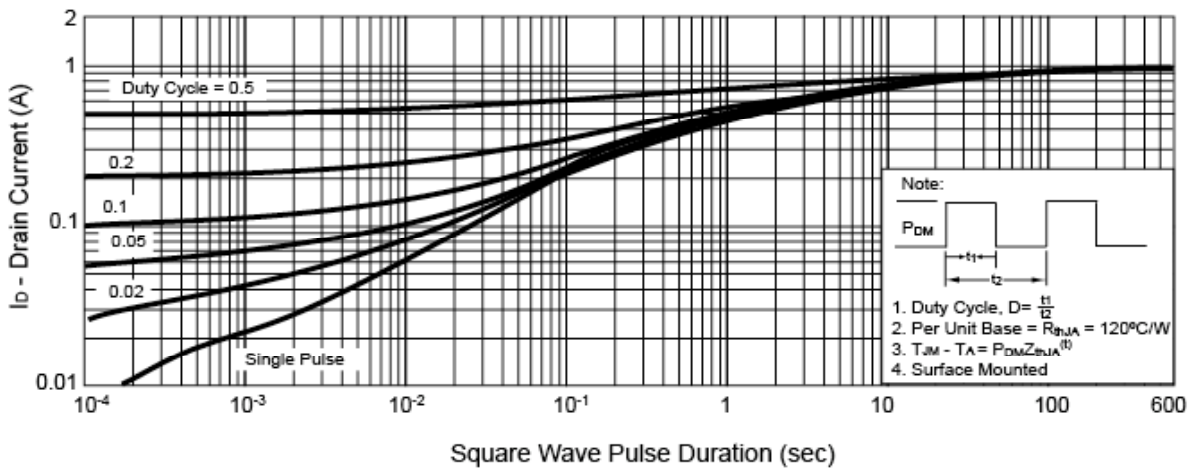
Threshold Voltage



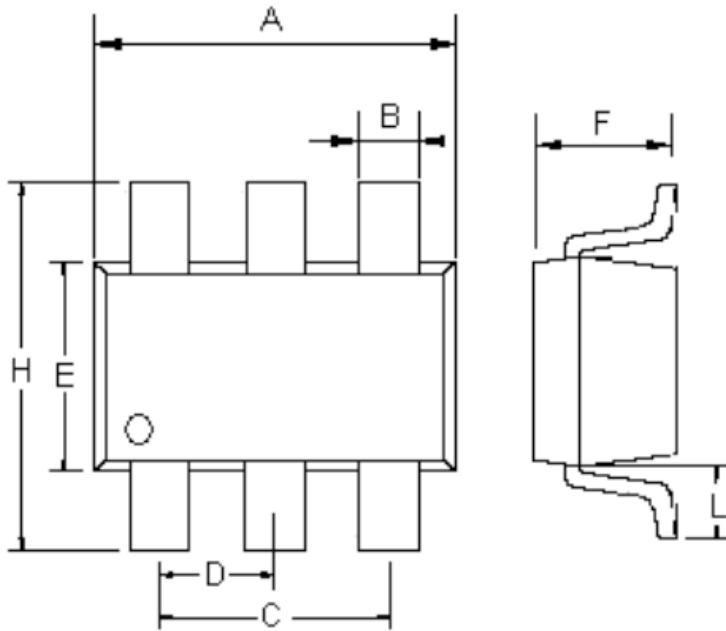
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



SOT-26 Mechanical Drawing



| SOT-26 DIMENSION | | | | |
|------------------|-------------|------|------------|-------|
| DIM | MILLIMETERS | | INCHES | |
| | MIN | MAX | MIN | MAX. |
| A | 2.70 | 3.00 | 0.106 | 0.118 |
| B | 0.25 | 0.50 | 0.010 | 0.020 |
| C | 1.90(typ) | | 0.075(typ) | |
| D | 0.95(typ) | | 0.037(typ) | |
| E | 1.50 | 1.70 | 0.059 | 0.067 |
| F | 1.05 | 1.35 | 0.041 | 0.053 |
| H | 2.60 | 3.00 | 0.102 | 0.118 |
| L | 0.60(typ) | | 0.024(typ) | |

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